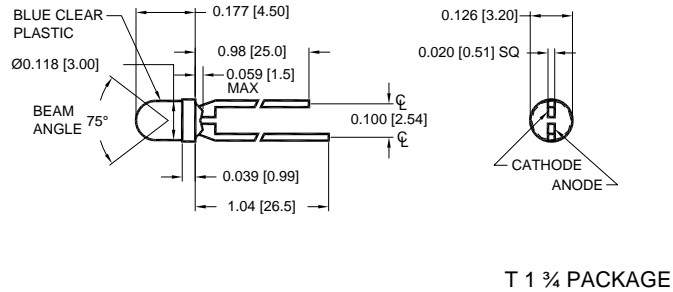


PACKAGE DIMENSIONS INCH [mm]



FEATURES

- High output power
- High reliability
- Medium emission angle

DESCRIPTION

The **PDI-E808-A** is a high power GaAlAs infrared emitter, packaged in a low cost T 1 ¾ plastic package.

APPLICATIONS

- Photoelectric switches
- Infrared sources
- Automatic controls

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
P_d	Power Dissipation		200	mW
I_f	Continuous Forward Current		100	mA
I_p	Peak Forward Current		1	A
V_r	Reverse Voltage		5	V
T_{STG}	Storage Temperature	-65	+125	°C
T_O	Operating Temperature	-65	+125	°C
T_s	Soldering Temperature*		+240	°C

* 1/16 inch from case for 3 seconds max.

ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
P_o	Radiant Intensity	$I_f = 100$ mA	12		30	mW/Sr
V_f	Forward Voltage	$I_f = 100$ mA		1.5	2.0	V
V_r	Reverse Breakdown Voltage	$I_f = 100$ μ A	5	30		V
λ_p	Peak Wavelength	$I_f = 50$ mA		880		nm
$\Delta\lambda$	Spectral Halfwidth	$I_f = 50$ mA		70		nm
C_t	Terminal Capacitance	$V_r = 0$ V, $f = 1$ MHz		20		pF
I_R	Reverse Current	$V_r = 4$ V		10		μ A
t_r	Rise Time	$I_f = 20$ mA		1.5		μ S
t_f	Fall Time	$I_f = 20$ mA		0.8		μ S

Information in this technical datasheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.